

Taiwan Semiconductor

3A, 45V - 60V Trench Schottky Surface Mount Rectifier

FEATURES

- AEC-Q101 qualified
- Patented Trench Schottky technology
- Excellent high temperature stability
- Low forward voltage
- Lower power loss/ high efficiency
- High forward surge capability
- Moisture sensitivity level: level 1, per J-STD-020
- RoHS Compliant
- Halogen-free according to IEC 61249-2-21

APPLICATIONS

- Low voltage, high freq. inverter
- DC/DC converter
- Freewheeling diodes
- Reverse battery protection
- Car lighting

MECHANICAL DATA

- Case: SOD-123HE
- Molding compound meets UL 94V-0 flammability rating
- Terminal: Matte tin plated leads, solderable per J-STD-002
- Meet JESD 201 class 2 whisker test
- Polarity: Indicated by cathode band
- Weight: 0.022g (approximately)

| KEY PARAMETERS | | | |
|--------------------|------------|------|--|
| PARAMETER | VALUE | UNIT | |
| ١ _F | 3 | А | |
| V _{RRM} | 45 - 60 | V | |
| I _{FSM} | 60 A | | |
| T _{J MAX} | 150 °C | | |
| Package | SOD-123HE | | |
| Configuration | Single die | | |





SOD-123HE



| ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}C$ unless otherwise noted) | | | | |
|---|---------------------|--------------|-----------|------|
| PARAMETER | SYMBOL | TSSE3H45H | TSSE3H60H | UNIT |
| Marking code on the device | | E3H45 | E3H60 | |
| Repetitive peak reverse voltage | V _{RRM} | 45 | 60 | V |
| Reverse voltage, total rms value | V _{R(RMS)} | 32 | 42 | V |
| Forward current | I _F | 3 | | А |
| Peak forward surge current, 8.3ms single half sine-wave superimposed on rated load | I _{FSM} | 60 | | А |
| Junction temperature | TJ | - 55 to +150 | | °C |
| Storage temperature | T _{STG} | - 55 to +150 | | °C |



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| THERMAL PERFORMANCE | | | |
|-------------------------------------|------------------|-----|------|
| PARAMETER | SYMBOL | ТҮР | UNIT |
| Junction-to-lead thermal resistance | R _{eJL} | 20 | °C/W |

| ELECTRICAL SPECIFICATIONS ($T_A = 25^{\circ}C$ unless otherwise noted) | | | | | | |
|--|-----------|---|------------------|------|------|------|
| PARAMETER | | CONDITIONS | SYMBOL | ТҮР | MAX | UNIT |
| Forward voltage ⁽¹⁾ | TSSE3H45H | $I_F = 3A, T_J = 25^{\circ}C$ | V _F | 0.47 | 0.57 | V |
| | | I _F = 3A, T _J = 125°C | | 0.40 | 0.50 | V |
| | TSSE3H60H | $I_F = 3A, T_J = 25^{\circ}C$ | | 0.50 | 0.60 | V |
| | | I _F = 3A, T _J = 125°C | | 0.43 | 0.53 | V |
| Reverse current @ rated $V_R^{(2)}$ | | $T_J = 25^{\circ}C$ | - I _R | - | 100 | μA |
| | | T _J = 125°C | | - | 25 | mA |

Notes:

1. Pulse test with PW = 0.3ms

2. Pulse test with PW = 30ms

| ORDERING INFORMATION | | |
|------------------------------|-----------|----------------------|
| ORDERING CODE ⁽¹⁾ | PACKAGE | PACKING |
| TSSE3HxH | SOD-123HE | 10,000 / Tape & Reel |

Notes:

1. "x" defines voltage from 45V(TSSE3H45H) to 60V(TSSE3H60H)



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CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

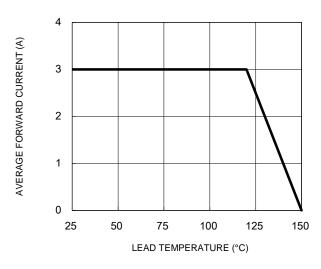
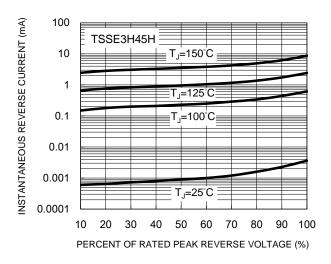
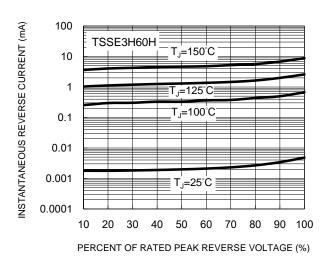


Fig.1 Forward Current Derating Curve

Fig.3 Typical Reverse Characteristics







1000 (g) 100 100 (g) 100 (

Fig.2 Typical Junction Capacitance

Fig.4 Typical Forward Characteristics

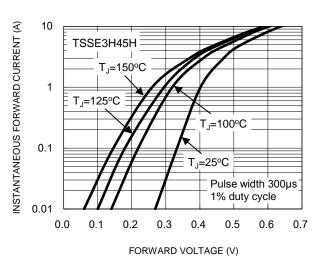
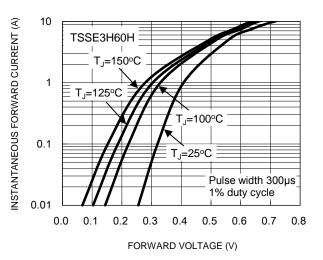


Fig.6 Typical Forward Characteristics

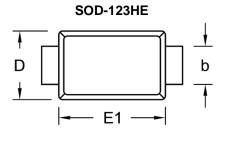


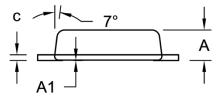


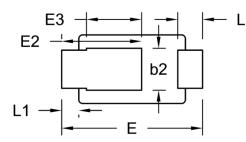
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PACKAGE OUTLINE DIMENSIONS

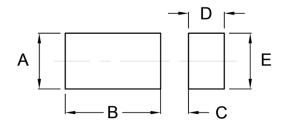






| DIM. | Unit (mm) | | Unit | (inch) |
|------|-----------|------|-------|--------|
| | Min. | Max. | Min. | Max. |
| A | 0.75 | 0.85 | 0.030 | 0.033 |
| A1 | 0.00 | 0.02 | 0.000 | 0.001 |
| b | 0.85 | 1.15 | 0.033 | 0.045 |
| b2 | 0.95 | 1.25 | 0.037 | 0.049 |
| с | 0.10 | 0.20 | 0.004 | 0.008 |
| D | 1.65 | 1.95 | 0.065 | 0.077 |
| E | 3.50 | 3.90 | 0.138 | 0.154 |
| E1 | 2.60 | 3.00 | 0.102 | 0.118 |
| E2 | 1.90 | 2.30 | 0.075 | 0.091 |
| E3 | 1.35 | 1.55 | 0.053 | 0.061 |
| L | 0.55 | 0.75 | 0.022 | 0.030 |
| L1 | 0.35 | 0.55 | 0.014 | 0.022 |

SUGGESTED PAD LAYOUT



| Symbol | Unit (mm) | Unit (inch) |
|--------|-----------|-------------|
| A | 1.40 | 0.055 |
| В | 2.40 | 0.094 |
| С | 0.70 | 0.028 |
| D | 0.90 | 0.035 |
| E | 1.40 | 0.055 |

MARKING DIAGRAM



| P/N | = Marking Code |
|-----|----------------|
|-----|----------------|

YW = Date Code

F = Factory Code



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